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# SLPS292 – JANUARY 2011

P-Channel NexFET<sup>™</sup> Power MOSFET

Check for Samples: CSD25303W1015

### FEATURES

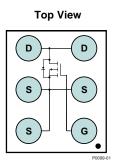
- Ultra Low Qg and Qgd
- Small Footprint
- Low Profile 0.62mm Height
- Pb Free
- RoHS Compliant
- Halogen Free
- CSP 1 × 1.5 mm Wafer Level Package

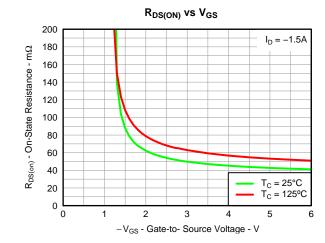
#### **APPLICATIONS**

- Battery Management
- Load Switch
- Battery Protection

### DESCRIPTION

The device has been designed to deliver the lowest on resistance and gate charge in the smallest outline possible with excellent thermal characteristics in an ultra low profile.





#### **PRODUCT SUMMARY**

T <sub>A</sub> = 25°	C unless otherwise stated	TYPICAL VA	UNIT			
V <sub>DS</sub>	Drain to Source Voltage -20					
Qg	Gate Charge Total (4.5V)	3.3	nC			
Q <sub>gd</sub>	Gate Charge Gate to Drain	0.6	nC			
		$V_{GS} = -1.8V$	72	mΩ		
R <sub>DS(on)</sub>	Drain to Source On Resistance	$V_{GS} = -2.5V$	56	mΩ		
		V <sub>GS</sub> = -4.5V 46		mΩ		
V <sub>GS(th)</sub>	Voltage Threshold	-0.65		V		

#### **ORDERING INFORMATION**

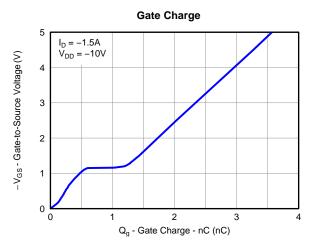
Device	Package	Media	Qty	Ship
CSD25303W1015	1 × 1.5 Wafer Level Package	7-inch reel	3000	Tape and Reel

#### ABSOLUTE MAXIMUM RATINGS

$T_A = 2$	5°C unless otherwise stated	VALUE	UNIT
V <sub>DS</sub>	Drain to Source Voltage	-20	V
$V_{GS}$	Gate to Source Voltage	±8	V
I <sub>D</sub>	Continuous Drain Current, $T_C = 25^{\circ}C^{(1)}$	-3	А
I <sub>DM</sub>	Pulsed Drain Current, $T_A = 25^{\circ}C^{(2)}$	-9	А
PD	Power Dissipation <sup>(1)</sup>	1.5	W
T <sub>STG</sub>	Storage Temperature Range	FF 4- 450	•
T <sub>J</sub> ,	Operating Junction Temperature Range	-55 to 150	°C

(1) Typical R<sub> $\theta$ JA</sub> = 90°C/W on 1in<sup>2</sup> Cu (2 oz.) on 0.060" thick FR4 PCB.

(2) Pulse width  $\leq 1$ ms, duty cycle  $\leq 2\%$ 



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

# ELECTRICAL CHARACTERISTICS

· A – 20	<sup>°</sup> C unless otherwise stated) PARAMETER	TEST CONDITIONS	MIN	ТҮР	MAX	UNIT	
Static C	haracteristics	TEST CONDITIONS					
		V 0V 1 250- A	20			V	
BV <sub>DSS</sub>	Drain to Source Voltage	$V_{GS} = 0V, I_D = -250\mu A$	-20				
I <sub>DSS</sub>	Drain to Source Leakage Current	$V_{GS} = 0V, V_{DS} = -16V$			-1	μA	
I <sub>GSS</sub>	Gate to Source Leakage Current	$V_{DS} = 0V, V_{GS} = \pm 8V$			-100	nA	
V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250 \mu A$	-0.4	-0.65	-1	V	
		$V_{GS} = -1.8V, I_D = -1.5A$		72	92	mΩ	
R <sub>DS(on)</sub>	Drain to Source On Resistance	$V_{GS} = -2.5V, I_D = -1.5A$		56	71	mΩ	
		$V_{GS} = -4.5V, I_D = -1.5A$		46	58	mΩ	
g <sub>fs</sub>	Transconductance	$V_{DS} = -10V, I_{D} = -1.5A$		9.6		S	
Dynamic	Characteristics						
C <sub>ISS</sub>	Input Capacitance			335	435	pF	
C <sub>OSS</sub>	Output Capacitance	V <sub>GS</sub> = 0V, V <sub>DS</sub> = -10V, f = 1MHz		149	191	pF	
C <sub>RSS</sub>	Reverse Transfer Capacitance			50	65	pF	
R <sub>g</sub>				0.6	1.2	Ω	
Qg	Gate Charge Total (-4.5V)			3.3	4.3	nC	
Q <sub>gd</sub>	Gate Charge Gate to Drain			0.6		nC	
Q <sub>gs</sub>	Gate Charge Gate to Source	$V_{\rm DS} = -10V, I_{\rm D} = -1.5A$		0.6		nC	
Q <sub>g(th)</sub>	Gate Charge at Vth			0.3		nC	
Q <sub>OSS</sub>	Output Charge	$V_{DS} = -11V, V_{GS} = 0V$		2.5		nC	
t <sub>d(on)</sub>	Turn On Delay Time			3.9		ns	
t <sub>r</sub>	Rise Time	V <sub>DS</sub> = -10V, V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -1.5A		8.6		ns	
t <sub>d(off)</sub>	Turn Off Delay Time	$R_{G} = 4\Omega$		11.3		ns	
t <sub>f</sub>	Fall Time			7.8		ns	
Diode C	haracteristics	· · · · · · · · · · · · · · · · · · ·	ŀ				
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> = -1.5A, V <sub>GS</sub> = 0V		-0.72	-1	V	
Q <sub>rr</sub>	Reverse Recovery Charge			3.6		nC	
t <sub>rr</sub>	Reverse Recovery Time	$V_{dd}$ = -11V, I <sub>F</sub> = -1.5A, di/dt = 200A/µs		11.3		ns	

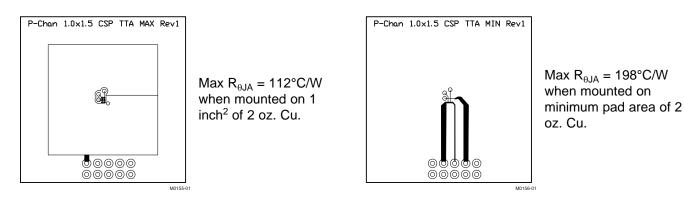
### THERMAL CHARACTERISTICS

$(T_A = 25^{\circ}C \text{ unless otherwise stated})$									
	PARAMETER	MIN	TYP	MAX	UNIT				
<b>D</b>	Thermal Resistance Junction to Ambient (Minimum Cu area)			198	°C/W				
R <sub>θJA</sub>	Thermal Resistance Junction to Ambient (1 in <sup>2</sup> Cu area)			112	°C/W				



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### **TYPICAL MOSFET CHARACTERISTICS**

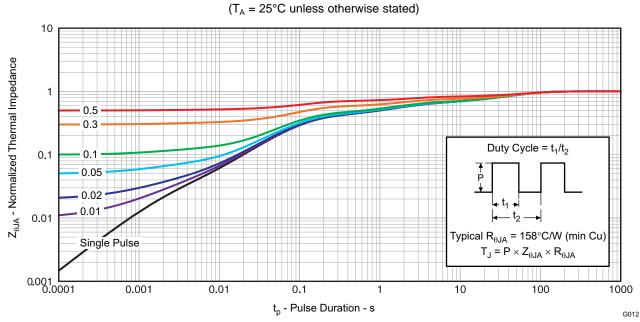
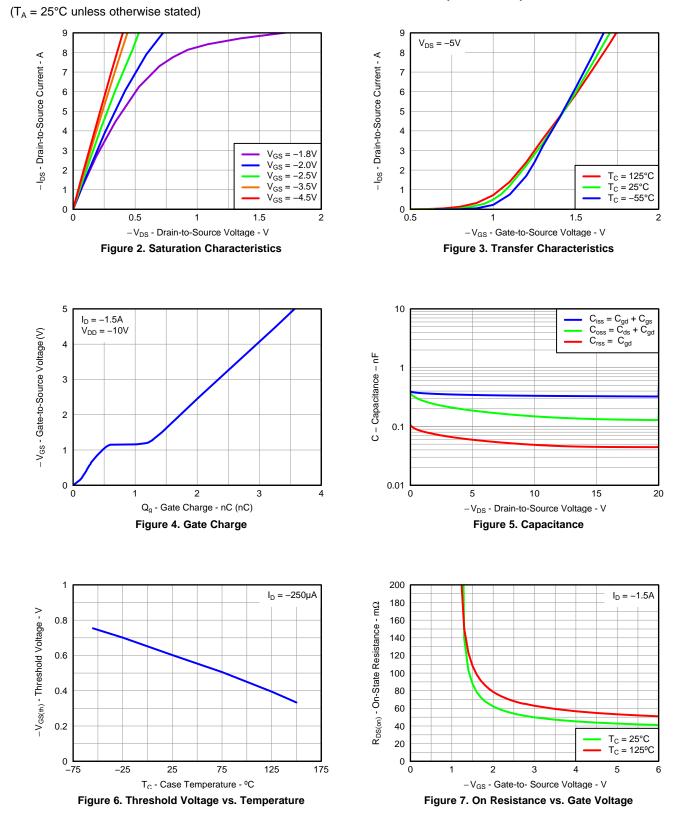


Figure 1. Transient Thermal Impedance

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#### **TYPICAL MOSFET CHARACTERISTICS (continued)**



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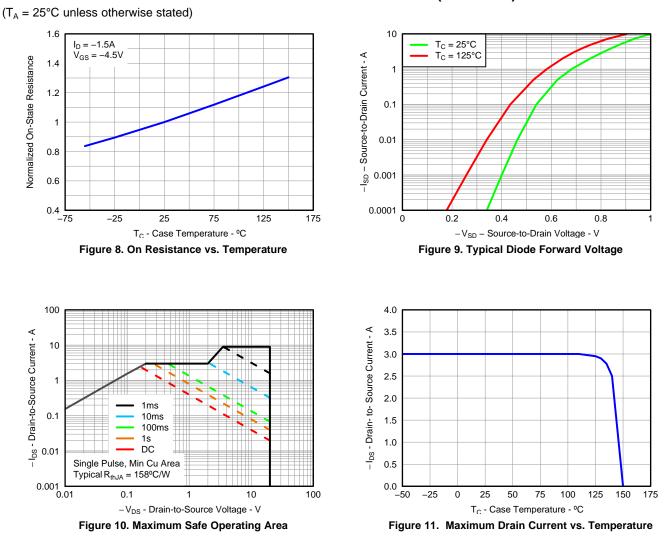
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#### **TYPICAL MOSFET CHARACTERISTICS (continued)**

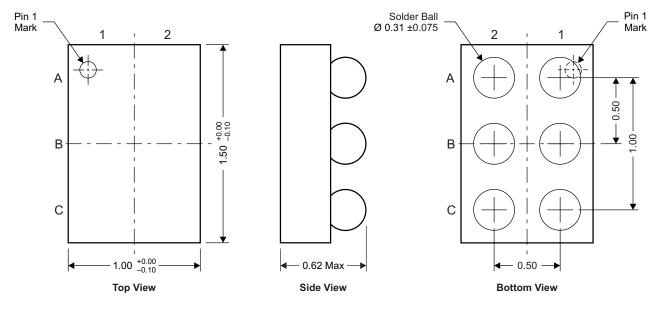


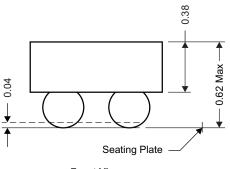
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#### **MECHANICAL DATA**







Front View

M0157-01

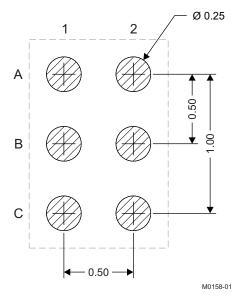
NOTE: All dimensions are in mm (unless otherwise specified)

Pinout						
POSITION	DESIGNATION					
C1, C2	Drain					
A1	Gate					
A2, B1, B2	Source					

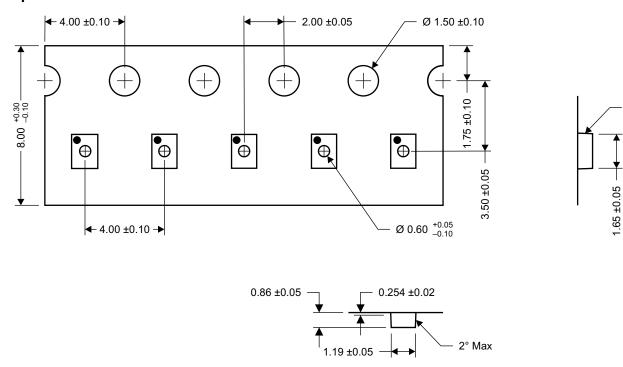


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#### Land Pattern Recommendation



NOTE: All dimensions are in mm (unless otherwise specified)



#### **Tape and Reel Information**

M0159-01

2° Max

NOTE: All dimensions are in mm (unless otherwise specified)



25-Feb-2014

## PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
CSD25303W1015	LIFEBUY	DSBGA	YZC	6	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-55 to 150		

<sup>(1)</sup> The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

<sup>(5)</sup> Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(<sup>6)</sup> Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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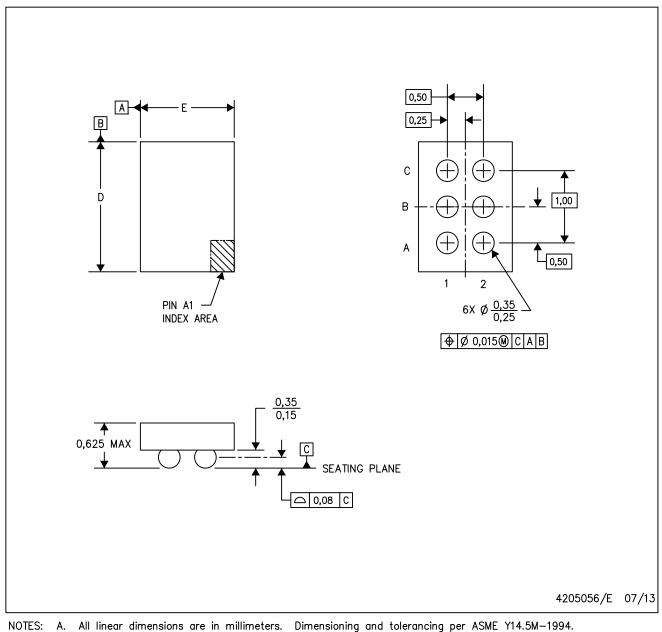
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PACKAGE OPTION ADDENDUM

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DIE-SIZE BALL GRID ARRAY



- B. This drawing is subject to change without notice.
- C. NanoFree™ package configuration.

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